

**SEMICONDUCTOR
TECHNICAL DATA**

KTB1241

EPITAXIAL PLANAR PNP TRANSISTOR

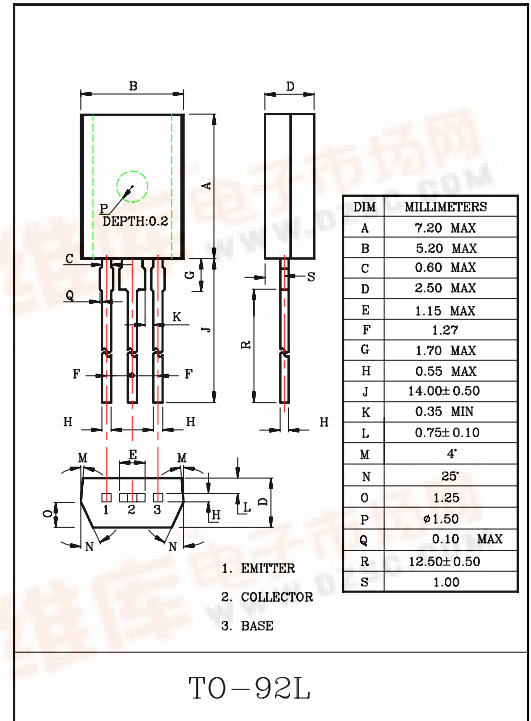
GENERAL PURPOSE APPLICATION.

FEATURE

- High Breakdown Voltage and High Current
: $V_{CE0}=-80V$, $I_C=-1A$.
- Low $V_{CE(sat)}$
- Complementary to KTD1863.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Emitter Current	I_E	1	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}C$

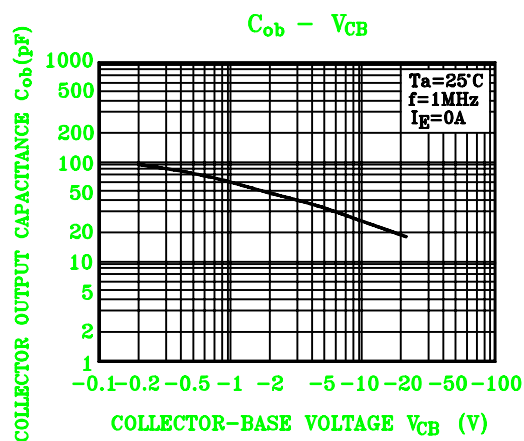
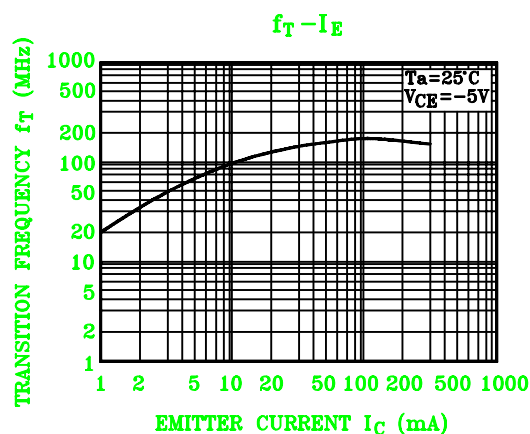
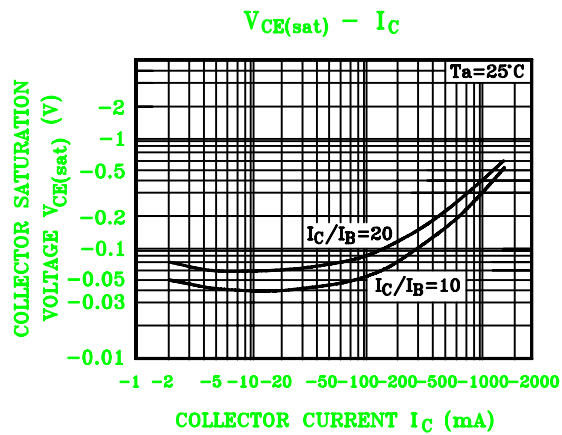
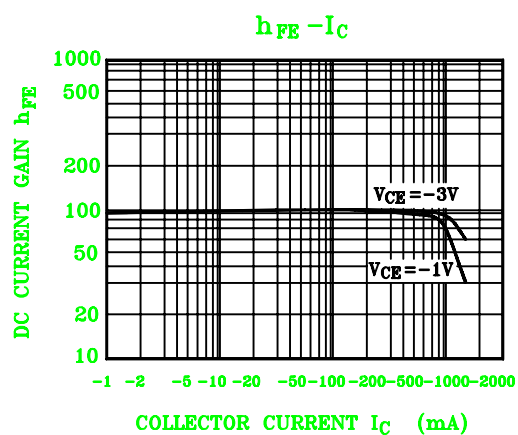
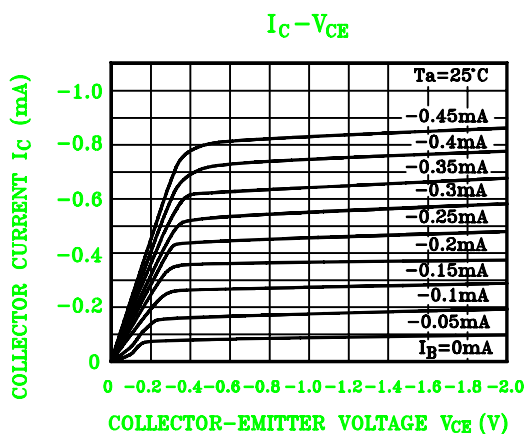
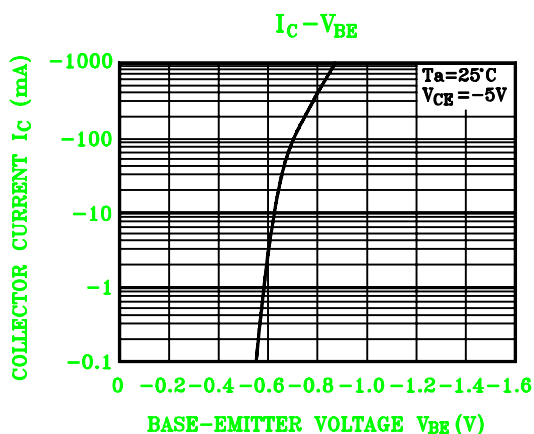


ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-60V$, $I_E=0$	-	-	-1	μA
Emitter-Cut-off Current	I_{EBO}	$V_{EB}=-4V$, $I_C=0$	-	-	-1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1mA$, $I_B=0$	-80	-	-	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=-3V$, $I_C=-100mA$	70	-	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$, $I_B=-50mA$	-	-	-0.4	V
Transition Frequency	f_T	$V_{CE}=-5V$, $I_E=50mA$, $f=30MHz$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$, $I_E=0$, $f=1MHz$	-	25	-	pF

Note : h_{FE} Classification O:70~140 , Y:120~240 , GR:200~400

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SAFE OPERATION AREA

